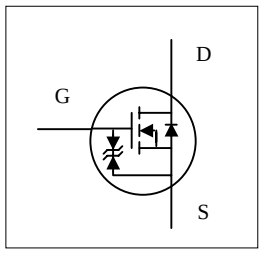
XP65CM220EH

Halogen-Free Product

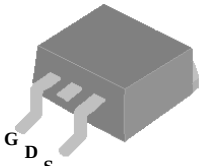
N-CHANNEL ENHANCEMENT MODE

POWER MOSFET

- **100% R_g & UIS Test**
- **Fast Switching Characteristic**
- **Simple Drive Requirement**
- **RoHS Compliant & Halogen-Free**



BV_{DSS}	650V
$R_{DS(ON)}$	0.22Ω
I_D[6]	20.5A



TO-252(H)

Description

XP65CM220E series are innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The TO-252 package is widely preferred for commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	±20	V
V_{GS}	Gate-Source Voltage, AC (f > 1Hz)	±30	V
I_D@T_C=25℃	Drain Current, V_{GS} @ 10V[6]	20.5	A
I_D@T_C=100℃	Drain Current, V_{GS} @ 10V[6]	12.9	A
I_{DM}	Pulsed Drain Current[1]	55	A
dv/dt	MOSFET dv/dt Ruggedness (V_{DS} = 0 …480V)	20	V/ns
P_D@T_C=25℃	Total Power Dissipation	104	W
P_D@T_A=25℃	Total Power Dissipation[5]	2	W
E_{AS}	Single Pulse Avalanche Energy[3]	200	mJ
dv/dt	Peak Diode Recovery dv/dt[4]	50	V/ns
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	1.2	℃/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient (PCB mount)[5]	62.5	℃/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=1mA	650	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V, I_D=5A	-	-	0.22	Ω
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	2	-	4	V
g_{fs}	Forward Transconductance	V_{DS}=10V, I_D=5A	-	13	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=520V, V_{GS}=0V	-	-	100	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±20V, V_{DS}=0V	-	-	±1	uA
Q_g	Total Gate Charge[7]	I_D=5A	-	33	52.8	nC
Q_{gs}	Gate-Source Charge[7]	V_{DS}=520V	-	7	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge[7]	V_{GS}=10V	-	12	-	nC
$t_{d(on)}$	Turn-on Delay Time[7]	V_{DD}=325V	-	14	-	ns
t_r	Rise Time[7]	I_D=5A	-	13	-	ns
$t_{d(off)}$	Turn-off Delay Time[7]	R_G=3.3Ω	-	67	-	ns
t_f	Fall Time[7]	V_{GS}=10V	-	17	-	ns
C_{iss}	Input Capacitance[7]	V_{GS}=0V	-	1380	2208	pF
C_{oss}	Output Capacitance[7]	V_{DS}=100V	-	35	-	pF
C_{rss}	Reverse Transfer Capacitance[7]	f=1.0MHz	-	10	-	pF
R_g	Gate Resistance	f=1.0MHz	-	9	18	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=5A, V_{GS}=0V	-	-	1.5	V
t_{rr}	Reverse Recovery Time[7]	I_S=5A, V_{GS}=0V	-	220	-	ns
Q_{rr}	Reverse Recovery Charge[7]	dI/dt=100A/μs	-	2	-	uC

Notes:

1.Pulse width limited by max. junction temperature.

2.Pulse test

3.Starting T_j=25°C , V_{DD}=90V , L=100mH , R_G=25Ω , V_{GS}=10V , I_{AS}=2A

4.I_{SD} ≦ I_D, V_{DD} ≦ BV_{DSS}, starting T_J = 25°C

5.Surface mounted on 1 in^2 copper pad of FR4 board

6.Limited by max. junction temperature. Maximum duty cycle D=0.5

7.Guaranteed by design.

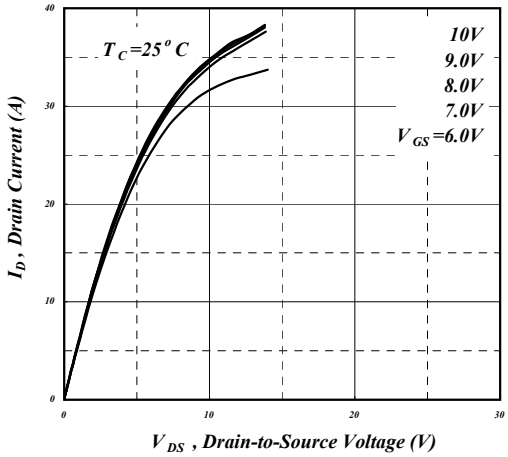


Fig 1. Typical Output Characteristics

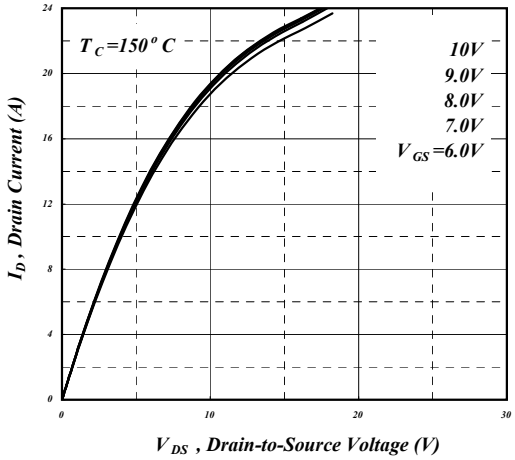


Fig 2. Typical Output Characteristics

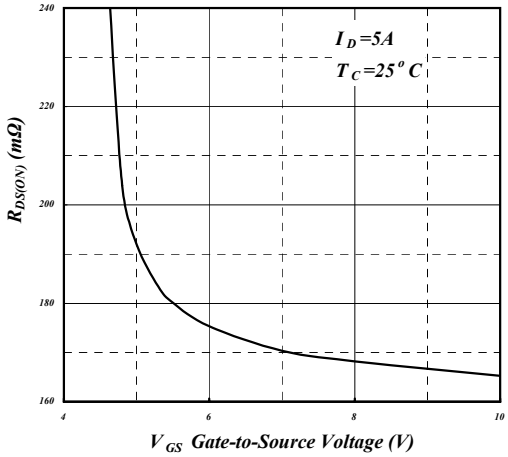


Fig 3. On-Resistance v.s. Gate Voltage

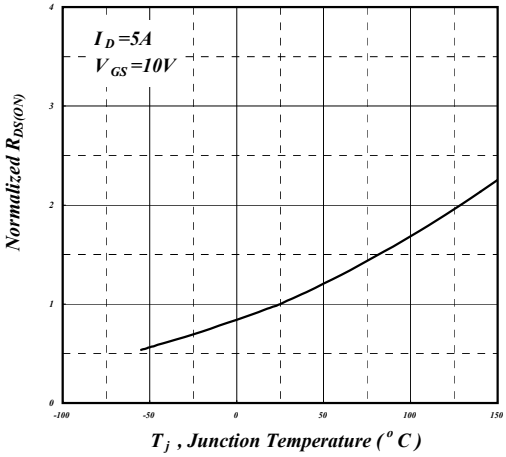


Fig 4. Normalized On-Resistance v.s. Junction Temperature

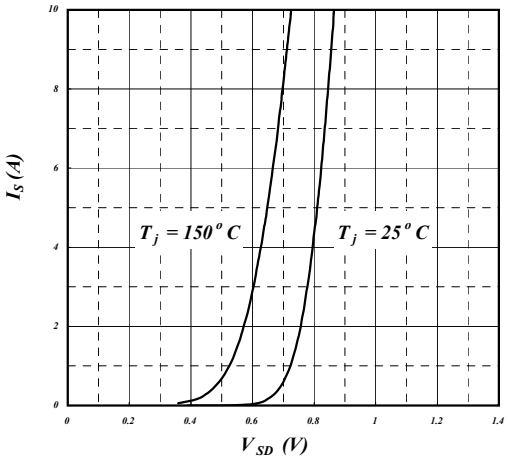


Fig 5. Forward Characteristic of Reverse Diode

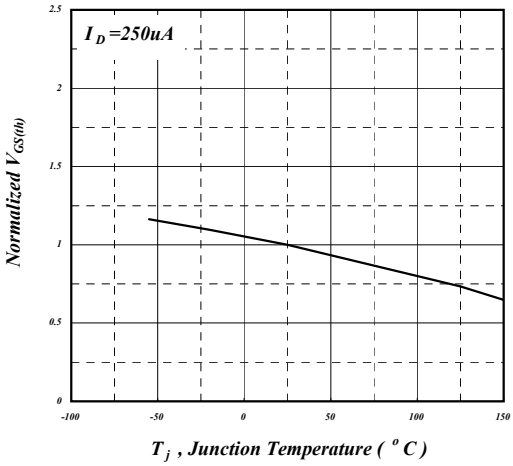


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

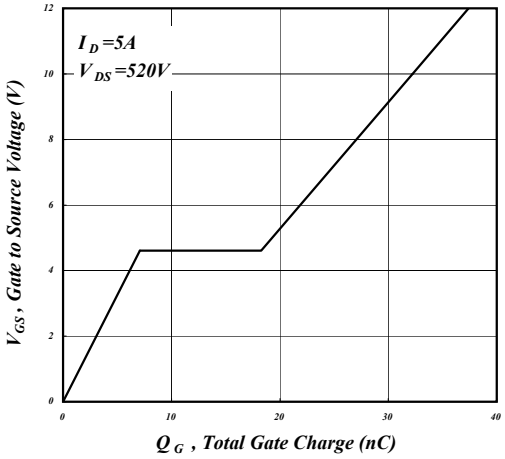


Fig 7. Gate Charge Characteristics

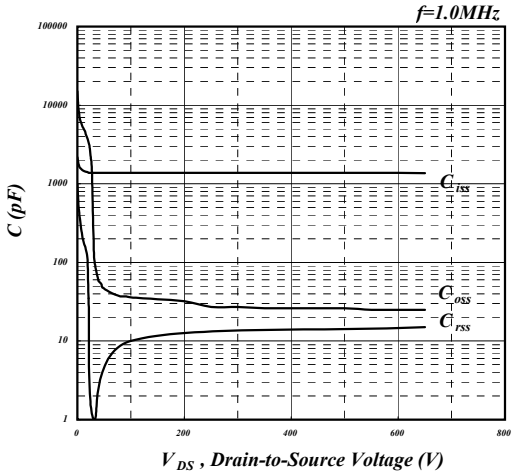


Fig 8. Typical Capacitance Characteristics

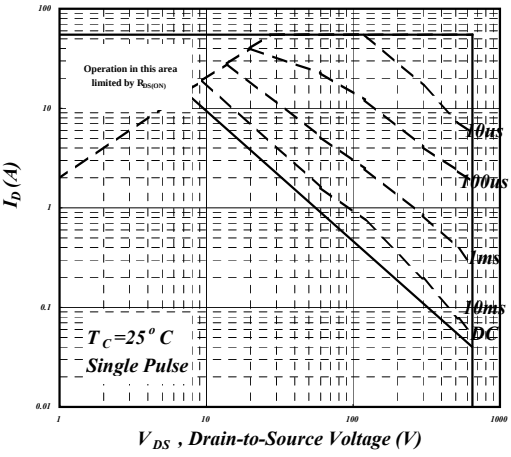


Fig 9. Maximum Safe Operating Area

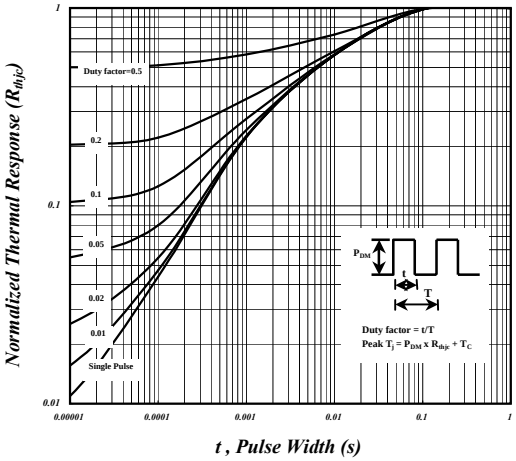


Fig10. Effective Transient Thermal Impedance

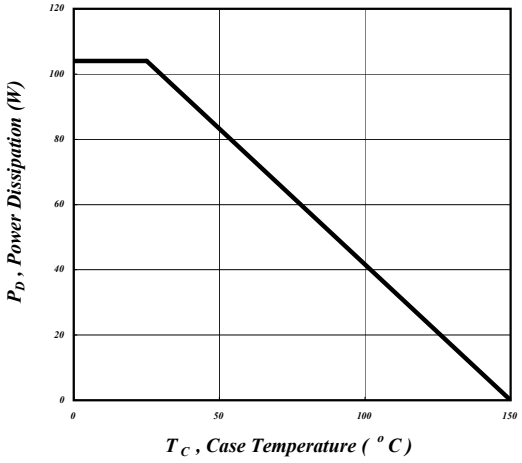


Fig 11. Total Power Dissipation

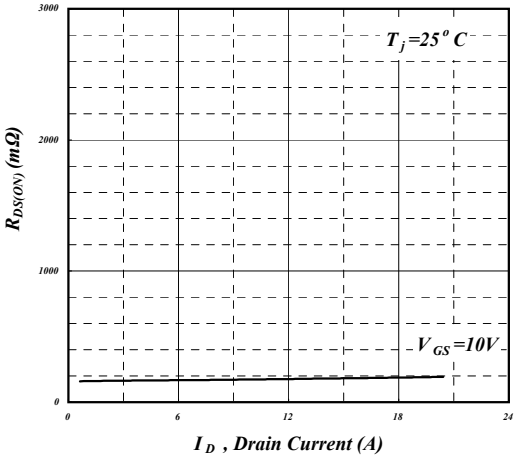


Fig 12. Typ. Drain-Source on State Resistance

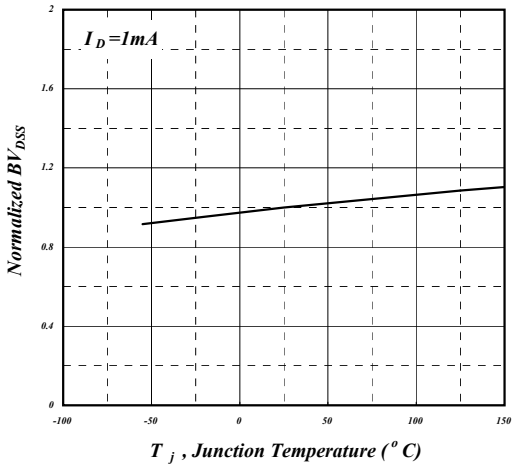


Fig 13. Normalized BV_{DSS} v.s. Junction Temperature